



ABSTRACT OF THE DISCLOSURE

There are disclosed a silicon seed crystal which is composed of silicon single crystal and used for the Czochralski method, wherein oxygen concentration in the seed crystal is 15 ppma (JEIDA) or less, a silicon seed crystal which is used for the Czochralski method, wherein the silicon seed crystal does not have a straight body, and a method for producing a silicon single crystal by the Czochralski method comprising using said seed crystal, bringing a tip end of the seed crystal into contact with a silicon melt to melt the tip end of the seed crystal, with or without performing necking operation, and growing a silicon single crystal. The method is capable of improving the rate of success in making crystals dislocation-free and the productivity of single crystal rods regardless of the use of necking operation.